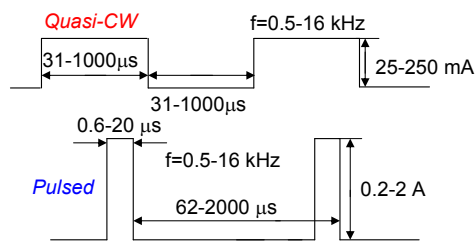
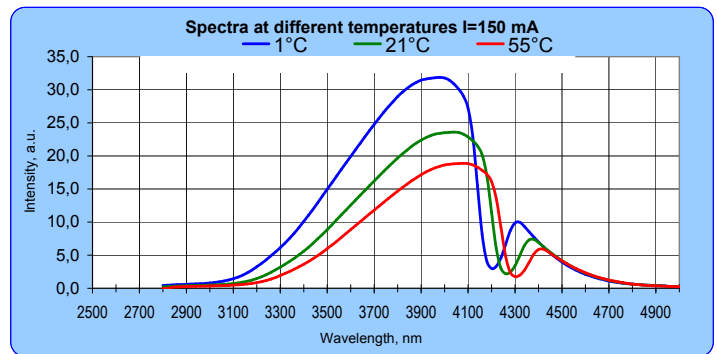
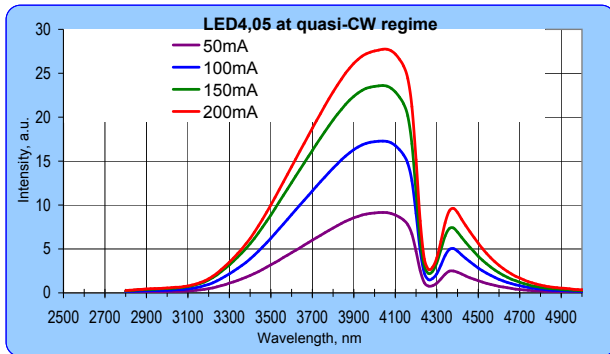


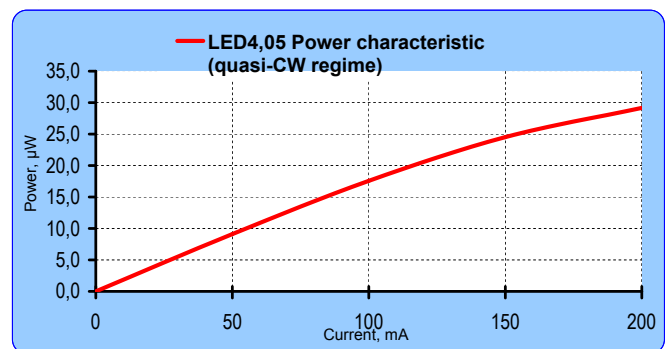
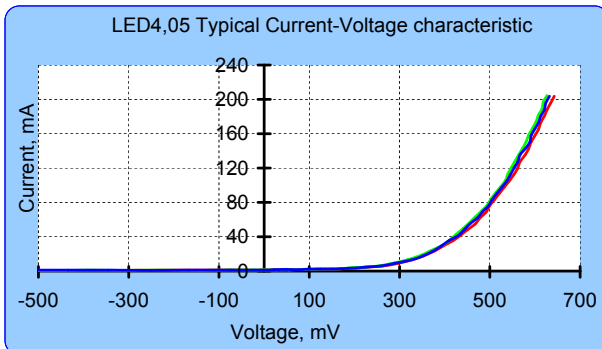
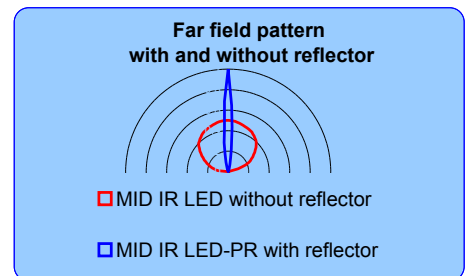
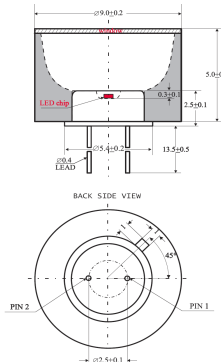


Light Emitting Diodes with central wavelength 4,1  $\mu\text{m}$  series are based on heterostructures grown on InAs substrates by MOCVD. InAsSb is used in the active layer. Wide band gap solid solutions InAsSbP with P content 50% are used for good electron confinement.

Parameters	Units	Conditions	Ratings		
			Min	Typ	Max
Peak emission wavelength	$\mu\text{m}$	T=300 K	3,95	4,05	4,10
FWHM of the emission band	nm	150 mA CW	700	850	1000
Quasi-CW Optical Power	$\mu\text{W}$	200 mA qCW	15	20	30
Pulsed Optical Power	$\mu\text{W}$	1 A	180	200	220
Switching Time	ns	T=300 K	10	20	30
Operating Temperature Range, $^{\circ}\text{C}$	-240 $^{\circ}$ + 50 $^{\circ}$				
Emitting Area, $\mu\text{m}$	300x300				
Soldering temperature	260 $^{\circ}\text{C}$				
Package					
TO-18 with a non-removable cap without a window			MID IR LED		
TO-18 with a parabolic reflector without a window			MID IR LED-PR		
TO-18 with a parabolic reflector with a window			<b>MID IR LED-PRwin</b>		
TO-5 with a built-in thermocooler and thermoresistor, covered by a cap with a window			MID IR LED-TEC		
TO-5 with a built-in thermocooler and thermoresistor, covered by a parabolic reflector with a window			MID IR LED-TEC-PR		



Maximum current is 220 mA at quasi-CW  
Maximum pulsed current is 1 A (duration 500 ns, repetition rate 2 kHz)  
Optimal operating current is 150-200 mA at quasi-CW.



**RELATED PRODUCTS**

- LED driver D-31M** can be used for LED power supply in quasi-CW and pulse modes
- LED driver mD-1c** can be used for LED power supply in a quasi-CW mode
- LED driver mD-1p** can be used for LED power supply in a pulse mode